International

ST330S SERIES

PHASE CONTROL THYRISTORS

Stud Version

Features

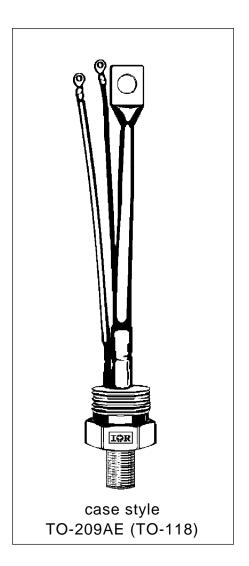
- Center amplifying gate
- Hermetic metal case with ceramic insulator
- International standard case TO-209AE (TO-118)
- Threaded studs UNF 3/4 16UNF2A or ISO M24x1.5
- Compression Bonded Encapsulation for heavy duty operations such as severe thermal cycling

Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

Major Ratings and Characteristics

Paramete	rs	ST330S	Units
I _{T(AV)}		330	А
	@ T _c	75	°C
I _{T(RMS)}		520	А
I _{TSM}	@ 50Hz	9000	А
	@ 60Hz	9420	А
l ² t	@ 50Hz	405	KA ² s
	@ 60Hz	370	KA ² s
V _{DRM} /V _{RRM}	1	400 to 1600	V
t _q	typical	100	μs
TJ		- 40 to 125	°C



330A

ELECTRICAL SPECIFICATIONS Voltage Ratings

Type number	Voltage Code	V _{DRM} /V _{RRM} , max. repetitive peak and off-state voltage V	V _{RSM} , maximum non- repetitive peak voltage V	I _{DRM} /I _{RRM} max. @ T _J = T _J max MA
	04	400	500	
	08	800	900	
ST330S	12	1200	1300	50
	14	1400	1500	
	16	1600	1700	

On-state Conduction

	Parameter	ST330S	Units	Conditions		
I _{T(AV)}	Max. average on-state current	330	А	180° condu	uction, half sine	e wave
,	@ Case temperature	75	°C			
I _{T(RMS)}	Max. RMS on-state current	520	А	DC @ 62°	C case tempera	ature
I _{TSM}	Max. peak, one-cycle	9000		t = 10ms	No voltage	
	non-repetitive surge current	9420	A	t = 8.3ms	reapplied	
		7570		t = 10ms	100% V _{RRM}	
		7920		t = 8.3ms	reapplied	Sinusoidal half wave,
l²t	Maximum I ² t for fusing	405		t = 10ms	No voltage	Initial T _J = T _J max.
		370	K ^ 20	(A ² s t = 8.3ms reapplied		
		287	NA S	t = 10ms	100% V _{RRM}	
		262		t = 8.3ms	reapplied	
l²√t	Maximum I ² \sqrt{t} for fusing	4050	KA²√s	t = 0.1 to 1	0ms, no voltag	je reapplied
V _{T(TO)1}	Low level value of threshold voltage	0.91	V	(16.7% x π	$x _{T(AV)} < l < \pi$	x I _{T(AV)}), T _J = T _J max.
V _{T(TO)2}	High level value of threshold voltage	0.92	V	$(I > \pi \times I_{T(A)})$	_{∨)}),T _J = T _J max	
r _{t1}	Low level value of on-state slope resistance	0.58	mΩ	(16.7% x π	$x _{T(AV)} < < \pi$	$x I_{T(AV)}), T_J = T_J max.$
r _{t2}	High level value of on-state slope resistance	0.57	11152	$(I > \pi \times I_{T(A)})$	_{∨)}),T _J = T _J max	
V _{TM}	Max. on-state voltage	1.51	V	I _{pk} = 1040A	$T_{J} = T_{J} \max$	$t_p = 10ms sine pulse$
I _H	Maximum holding current	600				
IL.	Typical latching current	1000	mA	$I_{\rm J} = 25^{\circ}\rm C$, anode supply	12V resistive load

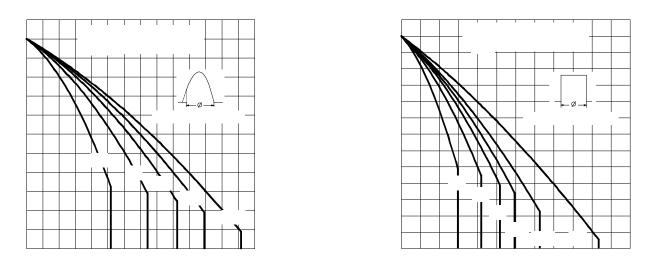




Fig. 2 - Current Ratings Characteristics

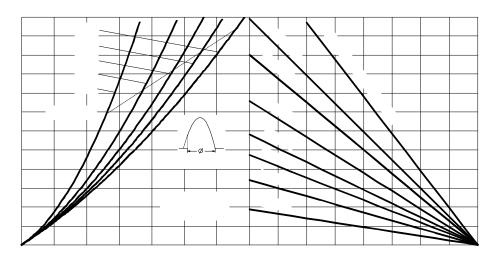
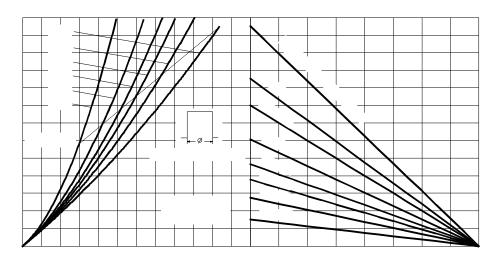
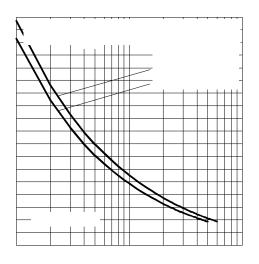


Fig. 3 - On-state Power Loss Characteristics





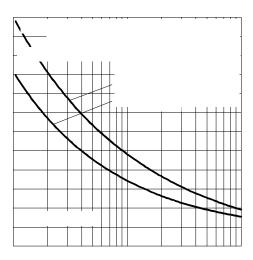
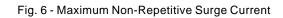


Fig. 5 - Maximum Non-Repetitive Surge Current



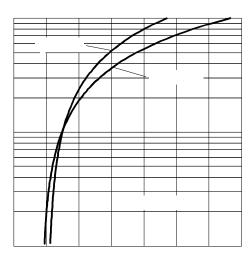
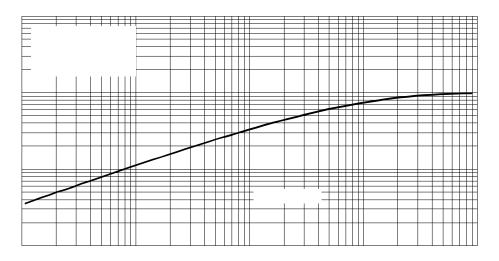


Fig. 7 - On-state Voltage Drop Characteristics



ST330S Series

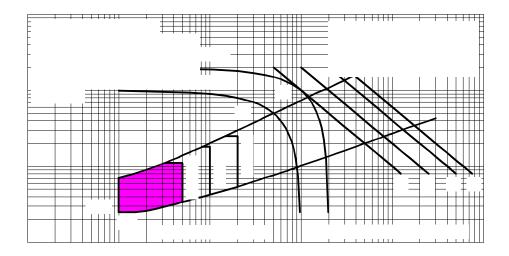


Fig. 9 - Gate Characteristics

Switching

	Parameter	ST330S	Units	Conditions
di/dt	Max. non-repetitive rate of rise of turned-on current	1000	A/µs	Gate drive 20V, 20 Ω , t _r \leq 1µs T _J = T _J max, anode voltage \leq 80% V _{DRM}
t _d	Typical delay time	1.0		Gate current A, di _g /dt = 1A/ μ s V _d = 0.67% V _{DRM} , T _J = 25°C
t _q	Typical turn-off time	100	μs	$I_{TM} = 550A, T_J = T_J max, di/dt = 40A/\mu s, V_R = 50V$ dv/dt = 20V/µs, Gate 0V 100 Ω , t _p = 500µs

Blocking

	Parameter	ST330S	Units	Conditions
dv/dt	Maximum critical rate of rise of off-state voltage	500	V ∕µs	$T_J = T_J$ max. linear to 80% rated V_{DRM}
I _{RRM} I _{DRM}	Max. peak reverse and off-state leakage current	50	mA	$T_J = T_J max$, rated V_{DRM}/V_{RRM} applied

Triggering

	Parameter	ST3	30S	Units	Conditions	
P _{GM}	Maximum peak gate power	10	.0	14/	T _J = T _J max, t _p	j ≤ 5ms
P _{G(AV)}	Maximum average gate power	2.	0	W	$T_J = T_J max, f$	= 50Hz, d% = 50
I _{GM}	Max. peak positive gate current	3.	0	Α	$T_J = T_J max, t_p$, ≤ 5ms
+V _{GM}	Maximum peak positive gate voltage	2	0	V	T T mov t	< 5mg
-V _{GM}	Maximum peak negative gate voltage	5.	0	V	$T_J = T_J max, t_p$	≤ 5ms
		TYP.	MAX.			
I _{GT}	DC gate current required	200	-		T _J = - 40°C	
	to trigger	100	200	mA	$T_J = 25^{\circ}C$	Max. required gate trigger/ cur-
		50	-		T _J = 125°C	rent/ voltage are the lowest value which will trigger all units 12V
V _{GT}	DC gate voltage required	2.5	-		T _J = - 40°C	anode-to-cathode applied
	to trigger	1.8	3.0	V	$T_J = 25^{\circ}C$	
		1.1	-		T _J = 125°C	
I _{GD}	DC gate current not to trigger	1(0	mA		Max. gate current/ voltage not to
V _{GD}	DC gate voltage not to trigger	0.2	25	V	T _J = T _J max	trigger is the max. value which will not trigger any unit with rated V _{DRM} anode-to-cathode applied

ST330S Series

Thermal and Mechanical Specification

	Parameter	ST330S	Units	Conditions	
Tj	Max. operating temperature range	-40 to 125			
T _{stg}	Max. storage temperature range	-40 to 150	°C		
R _{thJC}	Max. thermal resistance, junction to case	0.10	K/W	DC operation	
R _{thCS}	Max. thermal resistance, case to heatsink	0.03		Mounting surface, smooth, flat and greased	
Т	Mounting torque, ± 10%	48.5 (425)	Nm (lbf-in)	Non lubricated threads	
wt	Approximate weight	535	g		
	Case style	TO - 209AE (TO	-118)	See Outline Table	

$\Delta \mathrm{R}_{\mathrm{thJC}}$ Conduction

(The following table shows the increment of thermal resistence R_{thJC} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction	Rectangular conduction	Units	Conditions
180°	0.011	0.008		T _J = T _J max.
120°	0.013	0.014		
90°	0.017	0.018	K/W	
60°	0.025	0.026		
30°	0.041	0.041		

Ordering Information Table

Device Code	ST 33 0 S 16 P 0 1 2 3 4 5 6 7 8
1 - Thyristor	
2 - Essential par	t number
3 - 0 = Converte	r grade
4 - S = Compres	ssion bonding Stud
5 - Voltage code	e: Code x 100 = V _{RRM} (See Voltage Rating Table)
6 - P = Stud bas	se 16UNF threads
M = Stud bas	se metric threads (M24 x 1.5)
7 - 0 = Eyelet ter	rminals (Gate and Auxiliary Cathode Leads)
1 = Fast - on	terminals (Gate and Auxiliary Cathode Leads)
3 = Threaded	d top terminal 3/8" 24UNF-2A
8 - Critical dv/dt:	: None = 500V/µsec (Standard selection)
	L = 1000V/µsec (Special selection)

Outline Table

